## **CLAIMS**

- 1 1. A magnetic head, comprising:
- 2 a first magnetic pole;
- 3 a second magnetic pole;
- a write gap layer being disposed between said first and second magnetic poles,
- 5 where said write gap layer includes at least two sublayers, including an adhesion sublayer
- 6 and an electrically conductive, non-magnetic sublayer.
- 1 2. A magnetic head as described in claim 1 wherein said adhesion layer is disposed
- 2 upon said first magnetic pole, and said second magnetic pole is electroplated upon said
- 3 electrically conductive, non-magnetic sublayer.
- 1 3. A magnetic head as described in claim 2 wherein said electrically conductive,
- 2 non-magnetic sublayer serves as an electrical current conductor in a process for the
- 3 electroplating of said second magnetic pole.
- 1 4. A magnetic head as described in claim 1, wherein said adhesion sublayer is
- 2 comprised of a material selected from the group consisting of Ta, Ti, Cr and NiCr.
- 1 5. A magnetic head as described in claim 1 wherein said electrically conductive,
- 2 non-magnetic sublayer is comprised of a material selected from the group consisting of
- 3 Rh, Ru, Ir, Mo, W, Au, Be, Pd, Pt, Cu, PtMn, and Ta.

- 1 6. A magnetic head as described in claim 1 wherein said adhesion sublayer is
- 2 formed with a thickness of from approximately 25 Å to approximately 200 Å.
- 1 7. A magnetic head as described in claim 6 wherein said adhesion sublayer is
- 2 formed with a thickness of approximately 50 Å.
- 1 8. A magnetic head as described in claim 1 wherein said electrically conductive,
- 2 non-magnetic sublayer is formed with a thickness of from approximately 100 Å to
- 3 approximately 1000 Å.
- 1 9. A magnetic head as described in claim 6 wherein said electrically conductive,
- 2 non-magnetic sublayer is formed with a thickness of approximately 500 Å.
- 1 10. A magnetic head as described in claim 1 wherein said second magnetic pole is
- 2 comprised of a CoFe alloy.

1

- 2 11 A magnetic head as described in claim 1 wherein said write gap layer also
- 3 includes a third sublayer that is disposed between said adhesion sublayer and said
- 4 electrically conductive, non-magnetic sublayer, and wherein said third sublayer is
- 5 comprised of a material that is etchable in a reactive ion etch process.

- 1 12. A magnetic head as described in claim 11 wherein said third sublayer is formed
- with a thickness of from approximately 100 Å to approximately 1,000 Å.
- 1 13. A magnetic head as described in claim 12 wherein said third sublayer is formed
- with a thickness of approximately 600 Å.
- 3 14. A magnetic head as described in claim 11 wherein said third sublayer is
- 4 comprised of a material selected from the group consisting of Ta, Ti, W, Mo and Si.
- 1 15. A magnetic head as described in claim 1 wherein said adhesion layer is disposed
- 2 upon said first magnetic pole, and said second magnetic pole is electroplated upon said
- 3 electrically conductive, non-magnetic sublayer, where said electrically conductive, non-
- 4 magnetic sublayer serves as an electrical current conductor in a process for the
- 5 electroplating of said second magnetic pole;
- 6 wherein said adhesion sublayer is comprised of a material selected from the group
- 7 consisting of Ta, Ti, Cr and NiCr, and is formed with a thickness of from approximately
- 8 25 Å to approximately 200 Å;
- 9 wherein said electrically conductive, non-magnetic sublayer is comprised of a
- material selected from the group consisting of Rh, Ru, Ir, Mo, W, Au, Be, Pd, Pt, Cu,
- 11 PtMn, and Ta and is formed with a thickness of from approximately 100 Å to
- 12 approximately 1000 Å;
- wherein said write gap layer also includes a third sublayer that is disposed
- between said adhesion sublayer and said electrically conductive, non-magnetic sublayer,

- and wherein said third sublayer is comprised of a material that is etchable in a reactive
- ion etch process, and
- wherein said third sublayer is comprised of a material selected from the group
- consisting of Ta, Ti, W, Mo and Si, and is formed with a thickness of from approximately
- 19 100 Å to approximately 1,000 Å.
- 1 16. A hard disk drive, comprising:
- at least one hard disk being adapted for rotary motion upon a disk drive;
- at least one slider device having a slider body portion being adapted to fly over
- 4 said hard disk;
- a magnetic head being formed on said slider body for writing data to said hard
- 6 disk, said magnetic head including:
- 7 a first magnetic pole;
- 8 a second magnetic pole;
- a write gap layer being disposed between said first and second magnetic poles,
- where said write gap layer includes at least two sublayers, including an adhesion sublayer
- and an electrically conductive, non-magnetic sublayer.
- 1 17. A hard disk drive as described in claim 16 wherein said adhesion layer is disposed
- 2 upon said first magnetic pole, and said second magnetic pole is electroplated upon said
- 3 electrically conductive, non-magnetic sublayer.

- 1 18. A hard disk drive as described in claim 16 wherein said adhesion sublayer is
- 2 comprised of a material selected from the group consisting of Ta, Ti, Cr and NiCr.
- 1 19. A hard disk drive as described in claim 16 wherein said adhesion sublayer is
- 2 formed with a thickness of from approximately 25 Å to approximately 200 Å.
- 1 20. A hard disk drive as described in claim 16 wherein said electrically conductive,
- 2 non-magnetic sublayer is comprised of a material selected from the group consisting of
- 3 Rh, Ru, Ir, Mo, W, Au, Be, Pd, Pt, Cu, PtMn, and Ta.

4

- 1 21. A hard disk drive as described in claim 16 wherein said electrically conductive,
- 2 non-magnetic sublayer is formed with a thickness of from approximately 100 Å to
- 3 approximately 1000 Å.
- 1 22. A hard disk drive as described in claim 16 wherein said second magnetic pole is
- 2 comprised of a CoFe alloy.
- 3 23. A hard disk drive as described in claim 16 wherein said write gap layer also
- 4 includes a third sublayer that is disposed between said adhesion sublayer and said
- 5 electrically conductive, non-magnetic sublayer, and wherein said third sublayer is
- 6 comprised of a material that is etchable in a reactive ion etch process.

- 1 24. A hard disk drive as described in claim 23 wherein said third sublayer is formed
- with a thickness of from approximately 100 to approximately 1,000 Å.
- 1 25. A hard disk drive as described in claim 23 wherein said third sublayer is
- 2 comprised of a material selected from the group consisting of Ta, Ti, W, Mo and Si.
- 1 26. A method for fabricating a magnetic head, comprising:
- 2 fabricating a first magnetic pole upon a substrate surface;
- fabricating a write gap layer upon said first magnetic pole, including the
- 4 fabrication of an adhesion sublayer upon said first magnetic pole and the fabrication of an
- 5 electrically conductive, non-magnetic sublayer above said adhesion sublayer;
- 6 electroplating a second magnetic pole upon said electrically conductive, non-
- 7 magnetic sublayer, including the step of passing electrical current through said
- 8 electrically conductive, non-magnetic sublayer to plate up said second magnetic pole.
- 1 27. A method for fabricating a magnetic head as described in claim 26, wherein said
- 2 adhesion sublayer is comprised of a material selected from the group consisting of Ta, Ti,
- 3 Cr and NiCr, and is formed with a thickness of from approximately 25 Å to
- 4 approximately 200 Å.
- 1 28. A method for fabricating a magnetic head as described in claim 26 wherein said
- 2 electrically conductive, non-magnetic sublayer is comprised of a material selected from

- 3 the group consisting of Rh, Ru, Ir, Mo, W, Au, Be, Pd, Pt, Cu, PtMn, and Ta and is
- 4 formed with a thickness of from approximately 100 Å to approximately 1000 Å.
- 5 29. A method for fabricating a magnetic head as described in claim 26 including
- 6 fabricating a third sublayer between said adhesion sublayer and said electrically
- 7 conductive, non-magnetic sublayer, and wherein said third sublayer is comprised of a
- 8 material that is etchable in a reactive ion etch process.
- 1 30. A magnetic head as described in claim 29 wherein said third sublayer is
- 2 comprised of a material selected from the group consisting of Ta, Ti, W, Mo and Si, is
- 3 formed with a thickness of from approximately 100 Å to approximately 1,000 Å.